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(54) MANUFACTURE OF SILICON FILM

(57) Abstract:

characteristics by a method wherein a deposition rate and excellent electric PURPOSE: To form an amorphous silicon film having a sufficient

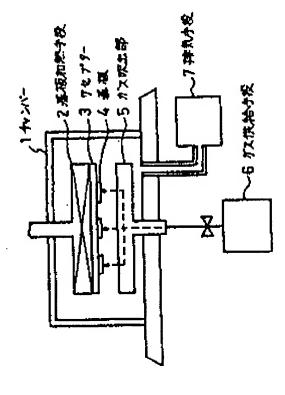
thermal CVD method is performed at the substrate temperature of 480°C or below using trisilane or higher silanes.

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inserted into the chamber 1 consisting gas blow- out hole 5, the exhaust hole atmospheric gas is introduced into the of a heating means 2, a susceptor 3, a chamber 1. As a result, an amorphous been stabilized, raw gas is introduced and the temperature variation when a substantially by performing a thermal When they are heated up to 400°C or decomposition reaction. At this time, thereabout by a heating means 2, the silicon film is formed on the surface exhaust means 7, they are placed on the upper surface of the susceptor 3. consisting of a wafer and the like is chamber 1 in advance, and after the silane of high order which is higher than trisilane is introduced into the CONSTITUTION: The substrate 4 temperature of the substrate 4 has film is formed can be made small and the like connected to a gas of the substrate 4 by thermal

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